MOSFET – Power, Single, P-Channel, ESD, μCool, UDFN, 1.6x1.6x0.55 mm -20 V, -5.0 A

Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 1.6x1.6x0.55 mm for Board Space Saving
- Lowest RDS(on) in 1.6x1.6 Package
- ESD Protected
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Load Switch
- PA Switch and Battery Switch
- Optimized for Power Management Applications for Portable Products, such as Cell Phones, PMP, DSC, GPS, and others

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage		V _{DSS}	-20	V	
Gate-to-Source Voltage		V _{GS}	±8.0	V	
Continuous Drain	Steady State	$T_A = 25^{\circ}C$	Ι _D	-4.0	А
Current (Note 1)		$T_A = 85^{\circ}C$		-2.9	
	t ≤ 5 s	$T_A = 25^{\circ}C$		-5.0	
Power Dissipa- tion (Note 1)	Steady State	$T_A = 25^{\circ}C$	PD	1.5	W
	t ≤ 5 s	T _A = 25°C		2.3	
Continuous Drain	Steady	T _A = 25°C	I _D	-2.6	А
Current (Note 2)	State	T _A = 85°C		-1.9	
Power Dissipation (Note 2) T _A = 25		$T_A = 25^{\circ}C$	PD	0.6	W
Pulsed Drain Current tp = 10 μs		I _{DM}	-17	А	
Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to 150	°C
Source Current (Body Diode) (Note 2)		۱ _S	-0.84	А	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		ΤL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

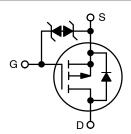
- Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
- Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.



ON Semiconductor®

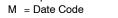
http://onsemi.com

MOSFET				
V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX		
	62 mΩ @ –4.5 V			
–20 V	95 mΩ @ −2.5 V	-5.0 A		
	140 mΩ @ −1.8 V	0.071		
	230 mΩ @ –1.5 V			



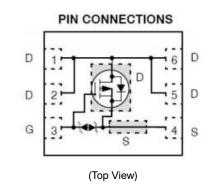
P-Channel MOSFET





= Pb–Free Package

(Note: Microdot may be in either location)



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 3)	R_{\thetaJA}	84	°C/W
Junction-to-Ambient – t \leq 5 s (Note 3)	$R_{\theta JA}$	55	
Junction-to-Ambient – Steady State min Pad (Note 4)	R_{\thetaJA}	200	

ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Units
OFF CHARACTERISTICS		•		•	•	-	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA		-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	$I_D = -250 \ \mu\text{A}, \text{ ref to } 25^{\circ}\text{C}$			-8.0		mV/°C
Zero Gate Voltage Drain Current	Current I_{DSS} $V_{GS} = 0 V$, T_{c}		$T_J = 25^{\circ}C$			-1.0	μA
		$V_{\rm DS} = -20$ V	$T_J = 85^{\circ}C$			-10	
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8.0 V$				±10	μA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS},$	I _D = -250 μA	-0.4		-1.0	V
Negative Threshold Temp. Coefficient	V _{GS(TH)} /T _J				3.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = -4.5 V	V, I _D = -4.0 A		54	62	mΩ
		V _{GS} = -2.5 V	V, I _D = -2.0 A		74	95	1
		V _{GS} = -1.8 ^v	V, I _D = -1.2 A		104	140	
		V _{GS} = -1.5 V	V, I _D = -0.5 A		137	230	
Forward Transconductance	9 FS	V _{DS} = -10 \	/, I _D = -3.0 A		10		S
CHARGES, CAPACITANCES & GATE	RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = -10 V			950		pF
Output Capacitance	C _{OSS}				90		
Reverse Transfer Capacitance	C _{RSS}				85		
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = -4.5 \text{ V}, V_{DS} = -10 \text{ V};$ $I_D = -3.0 \text{ A}$			12.3		nC
Threshold Gate Charge	Q _{G(TH)}				0.9		
Gate-to-Source Charge	Q _{GS}				1.6		
Gate-to-Drain Charge	Q _{GD}				3.3		
SWITCHING CHARACTERISTICS, VG	S = 4.5 V (Note 6)						
Turn-On Delay Time	t _{d(ON)}				7.9		ns
Rise Time	t _r	V _{CS} = -4.5 V.	Vpp = -10 V.		15.7		
Turn-Off Delay Time	t _{d(OFF)}				34.8		
Fall Time	t _f				28.5		
DRAIN-SOURCE DIODE CHARACTER	ISTICS	•		-	-		-
Forward Diode Voltage	VSD	V _{GS} = 0 V,	$T_J = 25^{\circ}C$		0.74	1.2	V
		VGS – 0 V,	T _J = 125°C		0.62		
Reverse Recovery Time	t _{RR}		1		11.8		ns
Charge Time	t _a	V _{GS} = 0 V, dis/dt = 100 A/µs, I _S = −1.0 A			8.5	1	
Discharge Time	t _b				3.3		

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces). 4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu. 5. Pulse Test: pulse width \leq 300 µs, duty cycle \leq 2%.

 $\mathsf{Q}_{\mathsf{R}\mathsf{R}}$

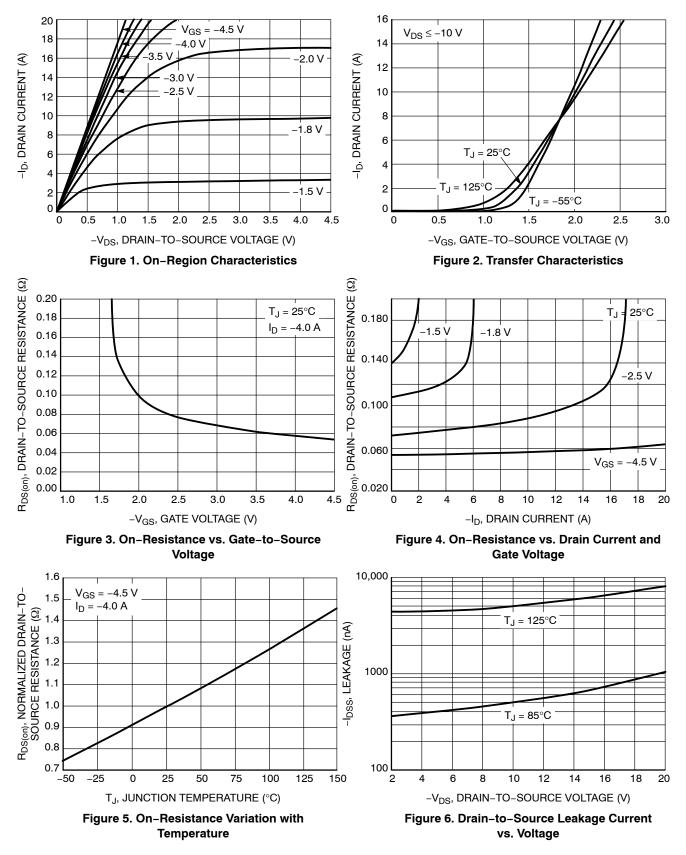
Reverse Recovery Charge

6. Switching characteristics are independent of operating junction temperatures.

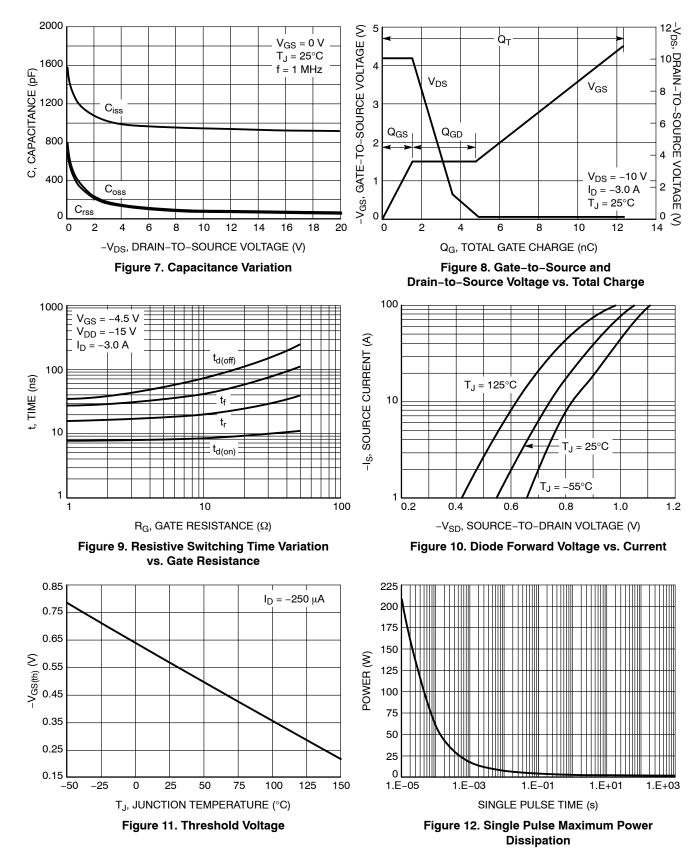
6.0

nC

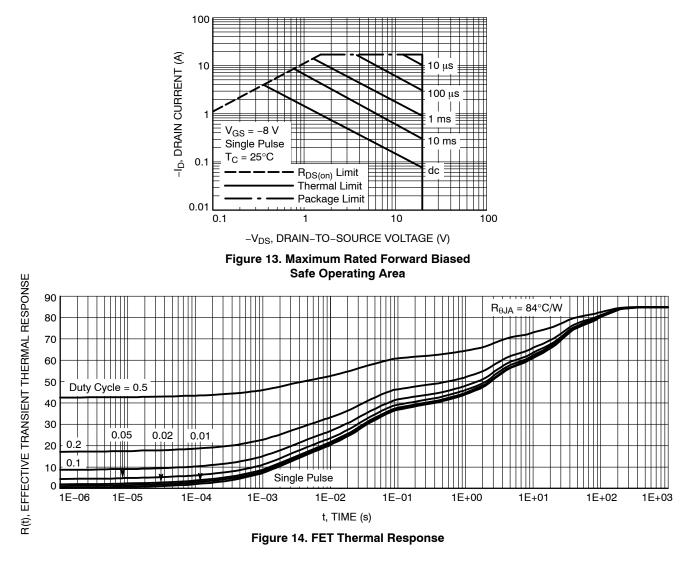
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

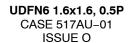


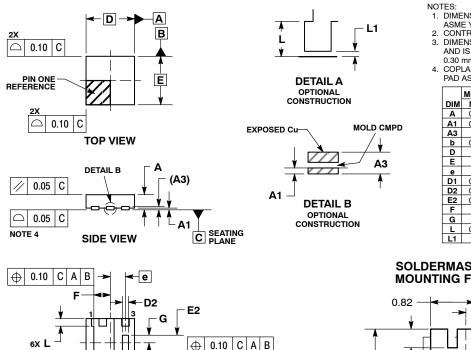
DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTLUS3A90PZTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS3A90PZTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS



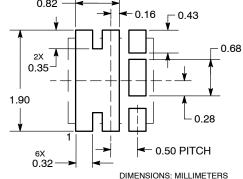


Α В

- 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND
- 0.30 mm FROM TERMINAL. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.13 REF			
b	0.20	0.30		
D	1.60 BSC			
E	1.60 BSC			
е	0.50 BSC			
D1	0.62	0.72		
D2	0.15	0.25		
E2	0.57	0.67		
F	0.55 BSC			
G	0.25 BSC			
L	0.20	0.30		
L1		0.15		

SOLDERMASK DEFINED **MOUNTING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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0.10

CAB

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6X b

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BOTTOM VIEW

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DETAIL A

D1

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